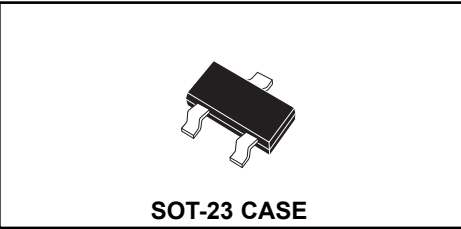


BCV47

NPN

SILICON DARLINGTON TRANSISTOR



CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BCV47 type is a Silicon NPN Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

Marking Code is FG.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

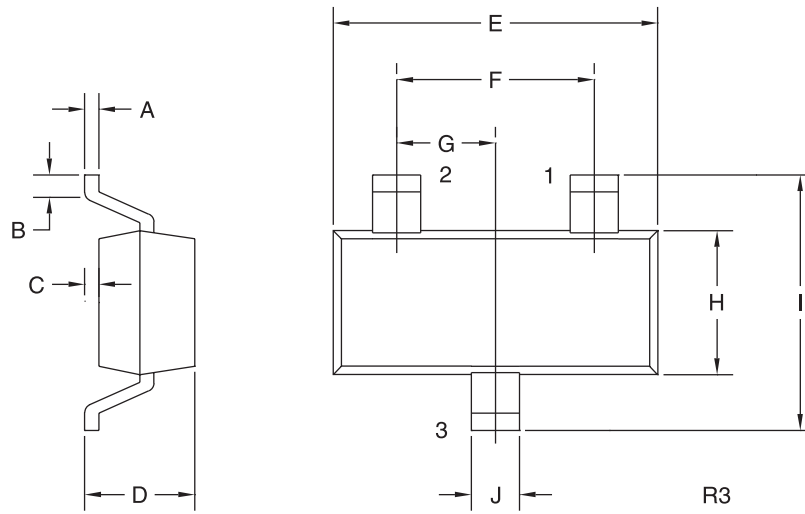
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Peak Collector Current	I_{CM}	800	mA
Base Current	I_B	100	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=30\text{V}$			100	nA
I_{EBO}	$V_{BE}=10\text{V}$			100	nA
BV_{CEO}	$I_C=10\text{mA}$	60			V
BV_{CBO}	$I_C=10\mu\text{A}$	80			V
BV_{EBO}	$I_E=100\text{nA}$	10			V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B = 0.1\text{mA}$			1.0	V
$V_{BE(SAT)}$	$I_C=100\text{mA}, I_B = 0.1\text{mA}$			1.5	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C = 1.0\text{mA}$	2,000			
h_{FE}	$V_{CE}=5.0\text{V}, I_C = 10\text{mA}$	4,000			
h_{FE}	$V_{CE}=5.0\text{V}, I_C = 100\text{mA}$	10,000			
f_T	$V_{CE}=5.0\text{V}, I_C = 30\text{mA}, f=100\text{MHz}$		220		MHz

R0 (07-December 2001)

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: FG

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)